

FEATURES

- 1 Ω typical on resistance
- 0.2 Ω on resistance flatness
- ± 3.3 V to ± 8 V dual supply operation
- 3.3 V to 16 V single supply operation
- No V_L supply required
- 3 V logic-compatible inputs
- Rail-to-rail operation
- Continuous current per channel
 - LFCSP: 385 mA
 - TSSOP: 238 mA
- 16-lead TSSOP and 16-lead, 4 mm \times 4 mm LFCSP

APPLICATIONS

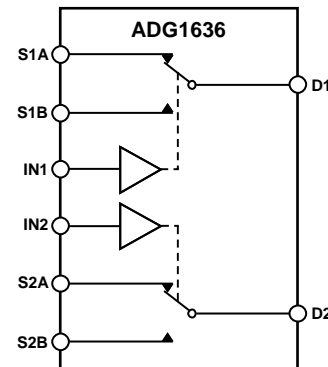
- Communication systems
- Medical systems
- Audio signal routing
- Video signal routing
- Automatic test equipment
- Data acquisition systems
- Battery-powered systems
- Sample-and-hold systems
- Relay replacements

GENERAL DESCRIPTION

The **ADG1636** is a monolithic CMOS device containing two independently selectable single-pole/double-throw (SPDT) switches. An EN input is used to enable or disable the device. When disabled, all channels are switched off. Each switch conducts equally well in both directions when on and has an input signal range that extends to the supplies. In the off condition, signal levels up to the supplies are blocked. Both switches exhibit break-before-make switching action for use in multiplexer applications.

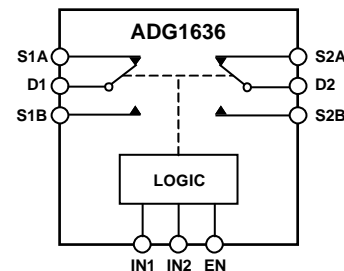
The ultralow on resistance of these switches make them ideal solutions for data acquisition and gain switching applications where low on resistance and distortion is critical. The on resistance profile is very flat over the full analog input range, ensuring excellent linearity and low distortion when switching audio signals.

FUNCTIONAL BLOCK DIAGRAMS



- NOTES
1. SWITCHES SHOWN FOR A LOGIC 1 INPUT.

Figure 1. 16-Lead TSSOP



- NOTES
1. SWITCHES SHOWN FOR A 1 INPUT LOGIC.

Figure 2. 16-Lead LFCSP

The CMOS construction ensures ultralow power dissipation, making the devices ideally suited for portable and battery-powered instruments.

PRODUCT HIGHLIGHTS

1. 1.6 Ω maximum on resistance over temperature.
2. Minimum distortion: THD + N = 0.007%.
3. 3 V logic-compatible digital inputs: $V_{INH} = 2.0$ V, $V_{INL} = 0.8$ V.
4. No V_L logic power supply required.
5. Ultralow power dissipation: <16 nW.
6. 16-lead TSSOP and 16-lead 4 mm \times 4 mm LFCSP.

Rev. B

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REVISION HISTORY

3/16—Rev. A to Rev. B

| | |
|--|------------|
| Changed CP-16-13 to CP-16-26 | Throughout |
| Changes to Figure 3, Figure 4, and Table 7 | 9 |
| Updated Outline Dimensions | 16 |
| Changes to Ordering Guide | 16 |

9/09—Rev. 0 to Rev. A

| | |
|-------------------------|---|
| Changes to Table 4..... | 6 |
|-------------------------|---|

1/09—Revision 0: Initial Version

SPECIFICATIONS

±5 V DUAL SUPPLY

$V_{DD} = +5\text{ V} \pm 10\%$, $V_{SS} = -5\text{ V} \pm 10\%$, GND = 0 V, unless otherwise noted.

Table 1.

| Parameter | 25°C | -40°C to +85°C | -40°C to +125°C | Unit | Test Conditions/Comments |
|--|------------|----------------|----------------------|-------------------|---|
| ANALOG SWITCH | | | | | |
| Analog Signal Range | | | V_{DD} to V_{SS} | V | |
| On Resistance (R_{ON}) | 1 | | | Ω typ | $V_S = \pm 4.5\text{ V}$, $I_S = -10\text{ mA}$; see Figure 23 |
| | 1.2 | 1.4 | 1.6 | Ω max | $V_{DD} = \pm 4.5\text{ V}$, $V_{SS} = \pm 4.5\text{ V}$ |
| On Resistance Match Between Channels (ΔR_{ON}) | 0.04 | | | Ω typ | $V_S = \pm 4.5\text{ V}$, $I_S = -10\text{ mA}$ |
| | 0.08 | 0.09 | 0.1 | Ω max | |
| On Resistance Flatness ($R_{FLAT(ON)}$) | 0.2 | | | Ω typ | $V_S = \pm 4.5\text{ V}$, $I_S = -10\text{ mA}$ |
| | 0.25 | 0.29 | 0.34 | Ω max | |
| LEAKAGE CURRENTS | | | | | |
| Source Off Leakage, I_S (Off) | ± 0.1 | | | nA typ | $V_{DD} = +5.5\text{ V}$, $V_{SS} = -5.5\text{ V}$ |
| | ± 0.25 | ± 1 | ± 4 | nA max | $V_S = \pm 4.5\text{ V}$, $V_D = \mp 4.5\text{ V}$; see Figure 24 |
| Drain Off Leakage, I_D (Off) | ± 0.1 | | | nA typ | $V_S = \pm 4.5\text{ V}$, $V_D = \mp 4.5\text{ V}$; see Figure 24 |
| | ± 0.25 | ± 2 | ± 10 | nA max | |
| Channel On Leakage, I_D , I_S (On) | ± 0.3 | | | nA typ | $V_S = V_D = \pm 4.5\text{ V}$; see Figure 25 |
| | ± 0.6 | ± 2 | ± 12 | nA max | |
| DIGITAL INPUTS | | | | | |
| Input High Voltage, V_{INH} | | | 2.0 | V min | |
| Input Low Voltage, V_{INL} | | | 0.8 | V max | |
| Input Current, I_{INL} or I_{INH} | 0.005 | | | μA typ | $V_{IN} = V_{GND}$ or V_{DD} |
| | | | ± 0.1 | μA max | |
| Digital Input Capacitance, C_{IN} | 5 | | | pF typ | |
| DYNAMIC CHARACTERISTICS¹ | | | | | |
| Transition Time, $t_{TRANSITION}$ | 130 | | | ns typ | $R_L = 300\ \Omega$, $C_L = 35\text{ pF}$ |
| | 209 | 245 | 273 | ns max | $V_S = 2.5\text{ V}$; see Figure 30 |
| t_{ON} (EN) | 119 | | | ns typ | $R_L = 300\ \Omega$, $C_L = 35\text{ pF}$ |
| | 148 | 166 | 176 | ns max | $V_S = 2.5\text{ V}$; see Figure 30 |
| t_{OFF} (EN) | 182 | | | ns typ | $R_L = 300\ \Omega$, $C_L = 35\text{ pF}$ |
| | 228 | 259 | 281 | ns max | $V_S = 2.5\text{ V}$; see Figure 30 |
| Break-Before-Make Time Delay, t_D | 30 | | | ns typ | $R_L = 300\ \Omega$, $C_L = 35\text{ pF}$ |
| | | | 17 | ns min | $V_{S1} = V_{S2} = 2.5\text{ V}$; see Figure 31 |
| Charge Injection | 130 | | | pC typ | $V_S = 0\text{ V}$, $R_S = 0\ \Omega$, $C_L = 1\text{ nF}$; see Figure 32 |
| Off Isolation | 70 | | | dB typ | $R_L = 50\ \Omega$, $C_L = 5\text{ pF}$, $f = 1\text{ MHz}$; see Figure 26 |
| Channel-to-Channel Crosstalk | 90 | | | dB typ | $R_L = 50\ \Omega$, $C_L = 5\text{ pF}$, $f = 1\text{ MHz}$; see Figure 28 |
| Total Harmonic Distortion + Noise (THD + N) | 0.007 | | | % typ | $R_L = 110\ \Omega$, 5 V p-p, $f = 20\text{ Hz}$ to 20 kHz; see Figure 29 |
| -3 dB Bandwidth | 25 | | | MHz typ | $R_L = 50\ \Omega$, $C_L = 5\text{ pF}$; see Figure 27 |
| C_S (Off) | 68 | | | pF typ | $V_S = 0\text{ V}$, $f = 1\text{ MHz}$ |
| C_D (Off) | 127 | | | pF typ | $V_S = 0\text{ V}$, $f = 1\text{ MHz}$ |
| C_D , C_S (On) | 220 | | | pF typ | $V_S = 0\text{ V}$, $f = 1\text{ MHz}$ |
| POWER REQUIREMENTS | | | | | |
| I_{DD} | 0.001 | | | μA typ | $V_{DD} = +5.5\text{ V}$, $V_{SS} = -5.5\text{ V}$ |
| | | | 1.0 | μA max | Digital inputs = 0 V or V_{DD} |
| V_{DD}/V_{SS} | | | $\pm 3.3/\pm 8$ | V min/max | |

¹ Guaranteed by design, not subject to production test.

12 V SINGLE SUPPLY

$V_{DD} = 12\text{ V} \pm 10\%$, $V_{SS} = 0\text{ V}$, $GND = 0\text{ V}$, unless otherwise noted.

Table 2.

| Parameter | 25°C | -40°C to +85°C | -40°C to +125°C | Unit | Test Conditions/Comments |
|--|------------|----------------|-----------------|-------------------|---|
| ANALOG SWITCH | | | | | |
| Analog Signal Range | | | 0 V to V_{DD} | V | |
| On Resistance (R_{ON}) | 0.95 | | | Ω typ | $V_S = 0\text{ V to }10\text{ V}$, $I_S = -10\text{ mA}$; see Figure 23 |
| | 1.1 | 1.25 | 1.45 | Ω max | $V_{DD} = 10.8\text{ V}$, $V_{SS} = 0\text{ V}$ |
| On Resistance Match Between Channels (ΔR_{ON}) | 0.03 | | | Ω typ | $V_S = 10\text{ V}$, $I_S = -10\text{ mA}$ |
| | 0.06 | 0.07 | 0.08 | Ω max | |
| On Resistance Flatness ($R_{FLAT(ON)}$) | 0.2 | | | Ω typ | $V_S = 0\text{ V to }10\text{ V}$, $I_S = -10\text{ mA}$ |
| | 0.23 | 0.27 | 0.32 | Ω max | |
| LEAKAGE CURRENTS | | | | | |
| Source Off Leakage, I_S (Off) | ± 0.1 | | | nA typ | $V_{DD} = 13.2\text{ V}$, $V_{SS} = 0\text{ V}$ $V_S = 1\text{ V}/10\text{ V}$, $V_S = 10\text{ V}/1\text{ V}$; see Figure 24 |
| | ± 0.25 | ± 1 | ± 4 | nA max | |
| Drain Off Leakage, I_D (Off) | ± 0.1 | | | nA typ | $V_S = 1\text{ V}/10\text{ V}$, $V_S = 10\text{ V}/1\text{ V}$; see Figure 24 |
| | ± 0.25 | ± 2 | ± 10 | nA max | |
| Channel On Leakage, I_D , I_S (On) | ± 0.3 | | | nA typ | $V_S = V_D = 1\text{ V or }10\text{ V}$; see Figure 25 |
| | ± 0.6 | ± 2 | ± 12 | nA max | |
| DIGITAL INPUTS | | | | | |
| Input High Voltage, V_{INH} | | | 2.0 | V min | |
| Input Low Voltage, V_{INL} | | | 0.8 | V max | |
| Input Current, I_{INL} or I_{INH} | 0.001 | | | μA typ | $V_{IN} = V_{GND}$ or V_{DD} |
| | | | ± 0.1 | μA max | |
| Digital Input Capacitance, C_{IN} | 5 | | | pF typ | |
| DYNAMIC CHARACTERISTICS¹ | | | | | |
| Transition Time, $t_{TRANSITION}$ | 100 | | | ns typ | $R_L = 300\ \Omega$, $C_L = 35\text{ pF}$ |
| | 153 | 183 | 206 | ns max | $V_S = 8\text{ V}$; see Figure 30 |
| t_{ON} (EN) | 80 | | | ns typ | $R_L = 300\ \Omega$, $C_L = 35\text{ pF}$ |
| | 95 | 103 | 110 | ns max | $V_S = 8\text{ V}$; see Figure 30 |
| t_{OFF} (EN) | 133 | | | ns typ | $R_L = 300\ \Omega$, $C_L = 35\text{ pF}$ |
| | 161 | 187 | 210 | ns max | $V_S = 8\text{ V}$; see Figure 30 |
| Break-Before-Make Time Delay, t_D | 25 | | | ns typ | $R_L = 300\ \Omega$, $C_L = 35\text{ pF}$ |
| | | | 17 | ns min | $V_{S1} = V_{S2} = 8\text{ V}$; see Figure 31 |
| Charge Injection | 150 | | | pC typ | $V_S = 6\text{ V}$, $R_S = 0\ \Omega$, $C_L = 1\text{ nF}$; see Figure 32 |
| Off Isolation | 70 | | | dB typ | $R_L = 50\ \Omega$, $C_L = 5\text{ pF}$, $f = 1\text{ MHz}$; see Figure 26 |
| Channel-to-Channel Crosstalk | 90 | | | dB typ | $R_L = 50\ \Omega$, $C_L = 5\text{ pF}$, $f = 1\text{ MHz}$; see Figure 28 |
| Total Harmonic Distortion + Noise (THD + N) | 0.013 | | | % typ | $R_L = 110\ \Omega$, 5 V p-p , $f = 20\text{ Hz to }20\text{ kHz}$; see Figure 29 |
| -3 dB Bandwidth | 27 | | | MHz typ | $R_L = 50\ \Omega$, $C_L = 5\text{ pF}$; see Figure 27 |
| C_S (Off) | 65 | | | pF typ | $V_S = 6\text{ V}$, $f = 1\text{ MHz}$ |
| C_D (Off) | 120 | | | pF typ | $V_S = 6\text{ V}$, $f = 1\text{ MHz}$ |
| C_D , C_S (On) | 216 | | | pF typ | $V_S = 6\text{ V}$, $f = 1\text{ MHz}$ |
| POWER REQUIREMENTS | | | | | |
| I_{DD} | 0.001 | | | μA typ | $V_{DD} = 12\text{ V}$ Digital inputs = 0 V or V_{DD} |
| | | | 1 | μA max | |
| I_{DD} | 230 | | | μA typ | Digital inputs = 5 V |
| | | | 360 | μA max | |
| V_{DD} | | | 3.3/16 | V min/max | |

¹ Guaranteed by design, not subject to production test.

5 V SINGLE SUPPLY

$V_{DD} = 5\text{ V} \pm 10\%$, $V_{SS} = 0\text{ V}$, $GND = 0\text{ V}$, unless otherwise noted.

Table 3.

| Parameter | 25°C | -40°C to +85°C | -40°C to 125°C | Unit | Test Conditions/Comments |
|--|------------|----------------|-----------------|-------------------|--|
| ANALOG SWITCH | | | | | |
| Analog Signal Range | | | 0 V to V_{DD} | V | |
| On Resistance (R_{ON}) | 1.7 | | | Ω typ | $V_S = 0\text{ V to }4.5\text{ V}$, $I_S = -10\text{ mA}$; see Figure 23 |
| | 2.15 | 2.4 | 2.7 | Ω max | $V_{DD} = 4.5\text{ V}$, $V_{SS} = 0\text{ V}$ |
| On Resistance Match Between Channels (ΔR_{ON}) | 0.05 | | | Ω typ | $V_S = 0\text{ V to }4.5\text{ V}$, $I_S = -10\text{ mA}$ |
| | 0.09 | 0.12 | 0.15 | Ω max | |
| On Resistance Flatness ($R_{FLAT(ON)}$) | 0.4 | | | Ω typ | $V_S = 0\text{ V to }4.5\text{ V}$, $I_S = -10\text{ mA}$ |
| | 0.53 | 0.55 | 0.6 | Ω max | |
| LEAKAGE CURRENTS | | | | | |
| Source Off Leakage, I_S (Off) | ± 0.05 | | | nA typ | $V_{DD} = 5.5\text{ V}$, $V_{SS} = 0\text{ V}$ |
| | ± 0.25 | ± 1 | ± 4 | nA max | $V_S = 1\text{ V}/4.5\text{ V}$, $V_D = 4.5\text{ V}/1\text{ V}$; see Figure 24 |
| Drain Off Leakage, I_D (Off) | ± 0.05 | | | nA typ | $V_S = 1\text{ V}/4.5\text{ V}$, $V_D = 4.5\text{ V}/1\text{ V}$; see Figure 24 |
| | ± 0.25 | ± 2 | ± 10 | nA max | |
| Channel On Leakage, I_D , I_S (On) | ± 0.1 | | | nA typ | $V_S = V_D = 1\text{ V or }4.5\text{ V}$; see Figure 25 |
| | ± 0.6 | ± 2 | ± 12 | nA max | |
| DIGITAL INPUTS | | | | | |
| Input High Voltage, V_{INH} | | | 2.0 | V min | |
| Input Low Voltage, V_{INL} | | | 0.8 | V max | |
| Input Current, I_{INL} or I_{INH} | 0.001 | | | μA typ | $V_{IN} = V_{GND}$ or V_{DD} |
| | | | ± 0.1 | μA max | |
| Digital Input Capacitance, C_{IN} | 5 | | | pF typ | |
| DYNAMIC CHARACTERISTICS¹ | | | | | |
| Transition Time, $t_{TRANSITION}$ | 160 | | | ns typ | $R_L = 300\ \Omega$, $C_L = 35\text{ pF}$ |
| | 271 | 319 | 355 | ns max | $V_S = 2.5\text{ V}$; see Figure 30 |
| t_{ON} (EN) | 132 | | | ns typ | $R_L = 300\ \Omega$, $C_L = 35\text{ pF}$ |
| | 172 | 185 | 201 | ns max | $V_S = 2.5\text{ V}$; see Figure 30 |
| t_{OFF} (EN) | 210 | | | ns typ | $R_L = 300\ \Omega$, $C_L = 35\text{ pF}$ |
| | 268 | 313 | 345 | ns max | $V_S = 2.5\text{ V}$; see Figure 30 |
| Break-Before-Make Time Delay, t_D | 30 | | | ns typ | $R_L = 300\ \Omega$, $C_L = 35\text{ pF}$ |
| | | | 17 | ns min | $V_{S1} = V_{S2} = 2.5\text{ V}$; see Figure 31 |
| Charge Injection | 70 | | | pC typ | $V_S = 2.5\text{ V}$, $R_S = 0\ \Omega$, $C_L = 1\text{ nF}$; see Figure 32 |
| Off Isolation | 70 | | | dB typ | $R_L = 50\ \Omega$, $C_L = 5\text{ pF}$, $f = 100\text{ kHz}$; see Figure 26 |
| Channel-to-Channel Crosstalk | 90 | | | dB typ | $R_L = 50\ \Omega$, $C_L = 5\text{ pF}$, $f = 100\text{ kHz}$; see Figure 28 |
| Total Harmonic Distortion + Noise (THD + N) | 0.09 | | | % typ | $R_L = 110\ \Omega$, $f = 20\text{ Hz to }20\text{ kHz}$, $V_S = 3.5\text{ V p-p}$; see Figure 29 |
| -3 dB Bandwidth | 26 | | | MHz typ | $R_L = 50\ \Omega$, $C_L = 5\text{ pF}$; see Figure 27 |
| C_S (Off) | 76 | | | pF typ | $V_S = 2.5\text{ V}$, $f = 1\text{ MHz}$ |
| C_D (Off) | 145 | | | pF typ | $V_S = 2.5\text{ V}$, $f = 1\text{ MHz}$ |
| C_D , C_S (On) | 237 | | | pF typ | $V_S = 2.5\text{ V}$, $f = 1\text{ MHz}$ |
| POWER REQUIREMENTS | | | | | |
| I_{DD} | 0.001 | | | μA typ | $V_{DD} = 5.5\text{ V}$ |
| | | 1.0 | 1.0 | μA max | Digital inputs = 0 V or V_{DD} |
| V_{DD} | | | 3.3/16 | V min/max | |

¹ Guaranteed by design, not subject to production test.

3.3 V SINGLE SUPPLY

$V_{DD} = 3.3\text{ V}$, $V_{SS} = 0\text{ V}$, $GND = 0\text{ V}$, unless otherwise noted.

Table 4.

| Parameter | 25°C | -40°C to +85°C | -40°C to +125°C | Unit | Test Conditions/Comments |
|--|------------|----------------|-----------------|-------------------|--|
| ANALOG SWITCH | | | | | |
| Analog Signal Range | | | 0 V to V_{DD} | V | |
| On Resistance (R_{ON}) | 3.2 | 3.4 | 3.6 | Ω typ | $V_S = 0\text{ V to }V_{DD}$, $I_S = -10\text{ mA}$; see Figure 23 $V_{DD} = 3.3\text{ V}$, $V_{SS} = 0\text{ V}$ |
| On Resistance Match Between Channels (ΔR_{ON}) | 0.06 | 0.07 | 0.08 | Ω typ | $V_S = 0\text{ V to }V_{DD}$, $I_S = -10\text{ mA}$ |
| On Resistance Flatness ($R_{FLAT(ON)}$) | 1.2 | 1.3 | 1.4 | Ω typ | $V_S = 0\text{ V to }V_{DD}$, $I_S = -10\text{ mA}$ |
| LEAKAGE CURRENTS | | | | | |
| Source Off Leakage, I_S (Off) | ± 0.02 | | | nA typ | $V_{DD} = 3.6\text{ V}$, $V_{SS} = 0\text{ V}$ $V_S = 0.6\text{ V}/3\text{ V}$, $V_D = 3\text{ V}/0.6\text{ V}$; see Figure 24 |
| | ± 0.25 | ± 1 | ± 4 | nA max | |
| Drain Off Leakage, I_D (Off) | ± 0.02 | | | nA typ | $V_S = 0.6\text{ V}/3\text{ V}$, $V_D = 3\text{ V}/0.6\text{ V}$; see Figure 24 |
| | ± 0.25 | ± 2 | ± 10 | nA max | |
| Channel On Leakage, I_D , I_S (On) | ± 0.05 | | | nA typ | $V_S = V_D = 0.6\text{ V or }3\text{ V}$; see Figure 25 |
| | ± 0.6 | ± 2 | ± 12 | nA max | |
| DIGITAL INPUTS | | | | | |
| Input High Voltage, V_{INH} | | | 2.0 | V min | |
| Input Low Voltage, V_{INL} | | | 0.8 | V max | |
| Input Current, I_{INL} or I_{INH} | 0.001 | | | μA typ | $V_{IN} = V_{GND}$ or V_{DD} |
| | | | ± 0.1 | μA max | |
| Digital Input Capacitance, C_{IN} | 5 | | | pF typ | |
| DYNAMIC CHARACTERISTICS¹ | | | | | |
| Transition Time, $t_{TRANSITION}$ | 275 | | | ns typ | $R_L = 300\ \Omega$, $C_L = 35\text{ pF}$ |
| | 449 | 506 | 550 | ns max | $V_S = 1.5\text{ V}$; see Figure 30 |
| t_{ON} (EN) | 225 | | | ns typ | $R_L = 300\ \Omega$, $C_L = 35\text{ pF}$ |
| | 306 | 327 | 338 | ns max | $V_S = 1.5\text{ V}$; see Figure 30 |
| t_{OFF} (EN) | 340 | | | ns typ | $R_L = 300\ \Omega$, $C_L = 35\text{ pF}$ |
| | 454 | 512 | 553 | ns max | $V_S = 1.5\text{ V}$; see Figure 30 |
| Break-Before-Make Time Delay, t_D | 50 | | | ns typ | $R_L = 300\ \Omega$, $C_L = 35\text{ pF}$ |
| | | | 28 | ns min | $V_{S1} = V_{S2} = 1.5\text{ V}$; see Figure 31 |
| Charge Injection | 50 | | | pC typ | $V_S = 1.5\text{ V}$, $R_S = 0\ \Omega$, $C_L = 1\text{ nF}$; see Figure 32 |
| Off Isolation | 70 | | | dB typ | $R_L = 50\ \Omega$, $C_L = 5\text{ pF}$, $f = 100\text{ kHz}$; see Figure 26 |
| Channel-to-Channel Crosstalk | 90 | | | dB typ | $R_L = 50\ \Omega$, $C_L = 5\text{ pF}$, $f = 100\text{ kHz}$; see Figure 28 |
| Total Harmonic Distortion + Noise (THD + N) | 0.19 | | | % typ | $R_L = 33\ \Omega$, $f = 20\text{ Hz to }20\text{ kHz}$, $V_S = 2\text{ V p-p}$; see Figure 29 |
| -3 dB Bandwidth | 26 | | | MHz typ | $R_L = 50\ \Omega$, $C_L = 5\text{ pF}$; see Figure 27 |
| C_S (Off) | 80 | | | pF typ | $V_S = 1.5\text{ V}$, $f = 1\text{ MHz}$ |
| C_D (Off) | 153 | | | pF typ | $V_S = 1.5\text{ V}$, $f = 1\text{ MHz}$ |
| C_D , C_S (On) | 243 | | | pF typ | $V_S = 1.5\text{ V}$, $f = 1\text{ MHz}$ |
| POWER REQUIREMENTS | | | | | |
| I_{DD} | 0.001 | | | μA typ | $V_{DD} = 3.6\text{ V}$ Digital inputs = 0 V or V_{DD} |
| | | 1.0 | 1.0 | μA max | |
| V_{DD} | | | 3.3/16 | V min/max | |

¹ Guaranteed by design, not subject to production test.

CONTINUOUS CURRENT PER CHANNEL, S OR D

Table 5.

| Parameter | 25°C | 85°C | 125°C | Unit |
|---|------|------|-------|------------|
| CONTINUOUS CURRENT, S OR D | | | | |
| $V_{DD} = +5\text{ V}, V_{SS} = -5\text{ V}$ | | | | |
| TSSOP ($\theta_{JA} = 150.4^\circ\text{C/W}$) | 238 | 151 | 88 | mA maximum |
| LFCSP ($\theta_{JA} = 48.7^\circ\text{C/W}$) | 385 | 220 | 105 | mA maximum |
| $V_{DD} = 12\text{ V}, V_{SS} = 0\text{ V}$ | | | | |
| TSSOP ($\theta_{JA} = 150.4^\circ\text{C/W}$) | 280 | 175 | 98 | mA maximum |
| LFCSP ($\theta_{JA} = 48.7^\circ\text{C/W}$) | 469 | 259 | 119 | mA maximum |
| $V_{DD} = 5\text{ V}, V_{SS} = 0\text{ V}$ | | | | |
| TSSOP ($\theta_{JA} = 150.4^\circ\text{C/W}$) | 189 | 126 | 77 | mA maximum |
| LFCSP ($\theta_{JA} = 48.7^\circ\text{C/W}$) | 301 | 182 | 98 | mA maximum |
| $V_{DD} = 3.3\text{ V}, V_{SS} = 0\text{ V}$ | | | | |
| TSSOP ($\theta_{JA} = 150.4^\circ\text{C/W}$) | 189 | 130 | 84 | mA maximum |
| LFCSP ($\theta_{JA} = 48.7^\circ\text{C/W}$) | 305 | 189 | 105 | mA maximum |

ABSOLUTE MAXIMUM RATINGS

$T_A = 25^\circ\text{C}$, unless otherwise noted.

Table 6.

| Parameter | Rating |
|---|--|
| V_{DD} to V_{SS} | 18 V |
| V_{DD} to GND | -0.3 V to +18 V |
| V_{SS} to GND | +0.3 V to -18 V |
| Analog Inputs ¹ | $V_{SS} - 0.3\text{ V}$ to $V_{DD} + 0.3\text{ V}$ or 30 mA, whichever occurs first |
| Digital Inputs ¹ | GND - 0.3 V to $V_{DD} + 0.3\text{ V}$ or 30 mA, whichever occurs first |
| Peak Current, S or D | 850 mA (pulsed at 1 ms, 10% duty cycle maximum) |
| Continuous Current, S or D ² | Data + 15% |
| Operating Temperature Range | |
| Industrial (Y Version) | -40°C to +125°C |
| Storage Temperature Range | -65°C to +150°C |
| Junction Temperature | 150°C |
| θ_{JA} Thermal Impedance | |
| 16-Lead TSSOP (2-Layer Board) | 150.4°C/W |
| 16-Lead LFCSP (4-Layer Board) | 48.7°C/W |
| Reflow Soldering Peak Temperature, Pb free | 260°C |

¹ Overvoltages at IN, S, or D are clamped by internal diodes. Current should be limited to the maximum ratings given.

² See Table 5.

Stresses at or above those listed under Absolute Maximum Ratings may cause permanent damage to the product. This is a stress rating only; functional operation of the product at these or any other conditions above those indicated in the operational section of this specification is not implied. Operation beyond the maximum operating conditions for extended periods may affect product reliability.

ESD CAUTION



ESD (electrostatic discharge) sensitive device. Charged devices and circuit boards can discharge without detection. Although this product features patented or proprietary protection circuitry, damage may occur on devices subjected to high energy ESD. Therefore, proper ESD precautions should be taken to avoid performance degradation or loss of functionality.

PIN CONFIGURATIONS AND FUNCTION DESCRIPTIONS

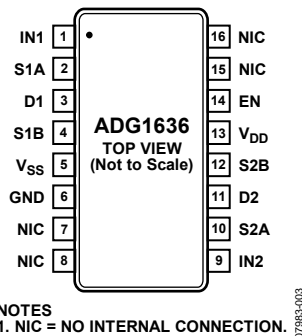


Figure 3. 16-Lead TSSOP Pin Configuration

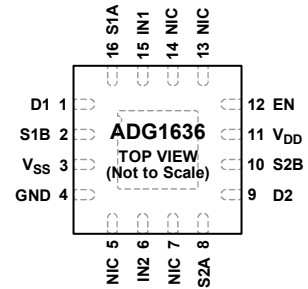


Figure 4. 16-Lead LFCSP Pin Configuration

Table 7. Pin Function Descriptions

| Pin No. | | Mnemonic | Description |
|------------------|--------------|-----------------|---|
| TSSOP | LFCSP | | |
| 1 | 15 | IN1 | Logic Control Input. |
| 2 | 16 | S1A | Source Terminal. This pin can be an input or output. |
| 3 | 1 | D1 | Drain Terminal. This pin can be an input or output. |
| 4 | 2 | S1B | Source Terminal. This pin can be an input or output. |
| 5 | 3 | V _{SS} | Most Negative Power Supply Potential. |
| 6 | 4 | GND | Ground (0 V) Reference. |
| 7, 8, 15, 16 | 5, 7, 13, 14 | NIC | No Internal Connection. |
| 9 | 6 | IN2 | Logic Control Input. |
| 10 | 8 | S2A | Source Terminal. This pin can be an input or output. |
| 11 | 9 | D2 | Drain Terminal. This pin can be an input or output. |
| 12 | 10 | S2B | Source Terminal. This pin can be an input or output. |
| 13 | 11 | V _{DD} | Most Positive Power Supply Potential. |
| 14 | 12 | EN | Active High Digital Input. When this pin is low, the device is disabled and all switches are off. When this pin is high, the Ax logic inputs determine the on switches. |
| N/A ¹ | 0 | EPAD | Exposed Pad. Tie the exposed pad to the substrate, V _{SS} . |

¹ N/A means not applicable.

Table 8. ADG1636 TSSOP Truth Table

| EN | IN _x | S _x A | S _x B |
|----|-----------------|------------------|------------------|
| 0 | X | Off | Off |
| 1 | 0 | Off | On |
| 1 | 1 | On | Off |

Table 9. ADG1636 LFCSP Truth Table

| EN | IN _x | S _x A | S _x B |
|----|-----------------|------------------|------------------|
| 0 | X | Off | Off |
| 1 | 0 | Off | On |
| 1 | 1 | On | Off |

TYPICAL PERFORMANCE CHARACTERISTICS

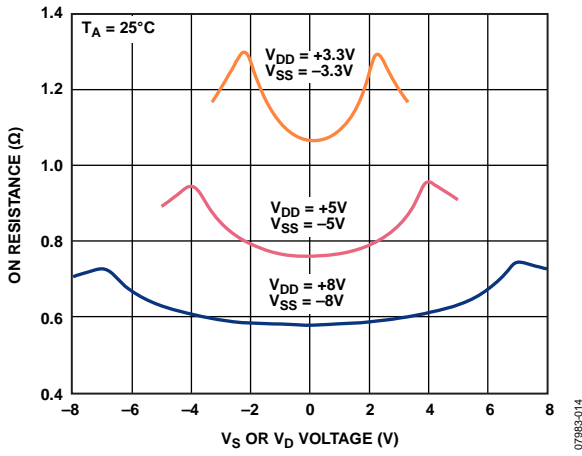


Figure 5. On Resistance as a Function of V_D (V_S) for Dual Supply

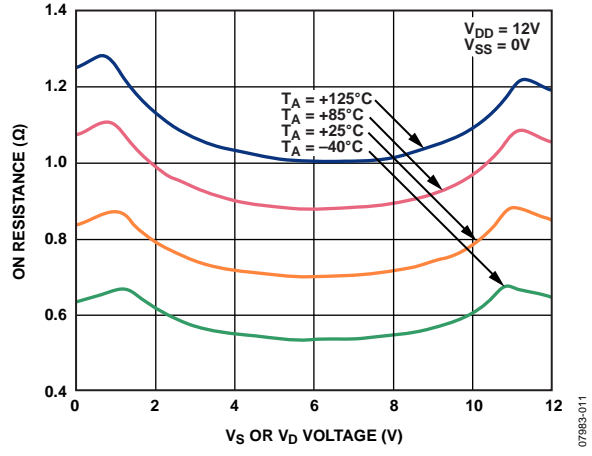


Figure 8. On Resistance as a Function of V_D (V_S) for Different Temperatures, 12 V Single Supply

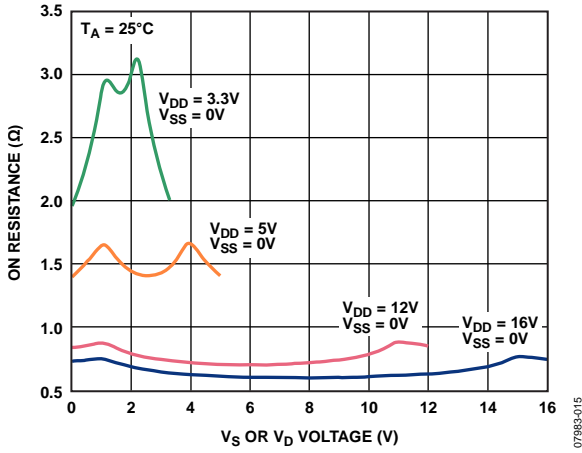


Figure 6. On Resistance as a Function of V_D (V_S) for Single Supply

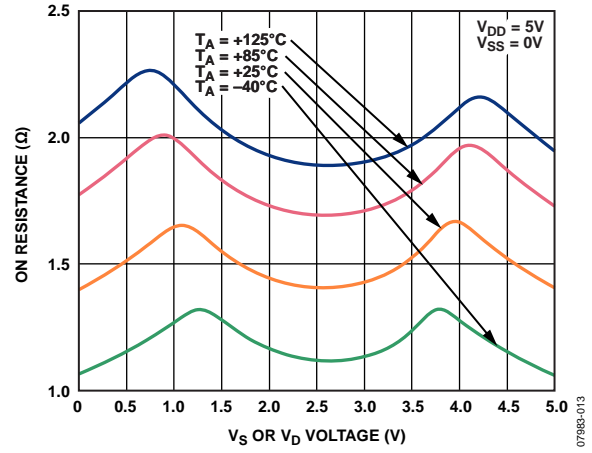


Figure 9. On Resistance as a Function of V_D (V_S) for Different Temperatures, 5 V Single Supply

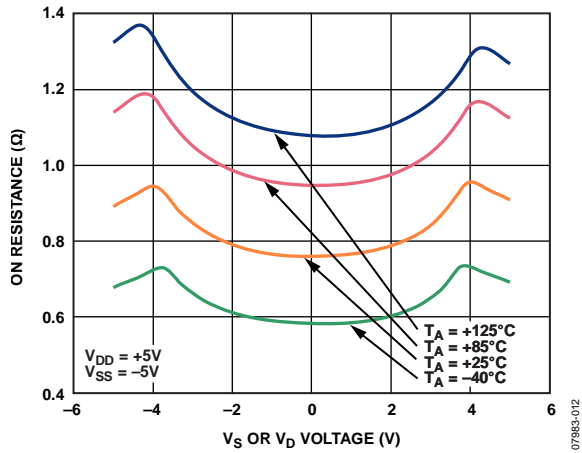


Figure 7. On Resistance as a Function of V_D (V_S) for Different Temperatures, ± 5 V Dual Supply

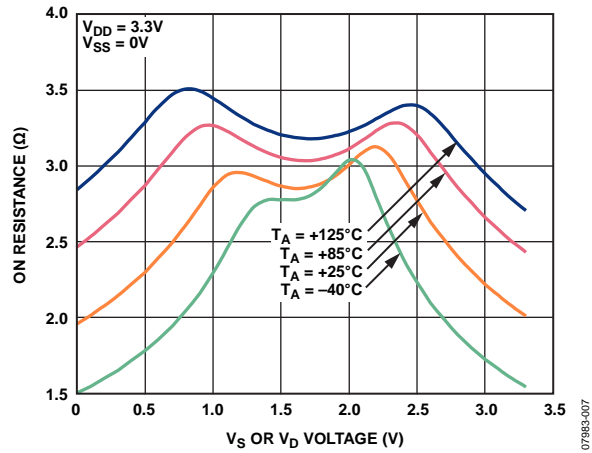


Figure 10. On Resistance as a Function of V_D (V_S) for Different Temperatures, 3.3 V Single Supply

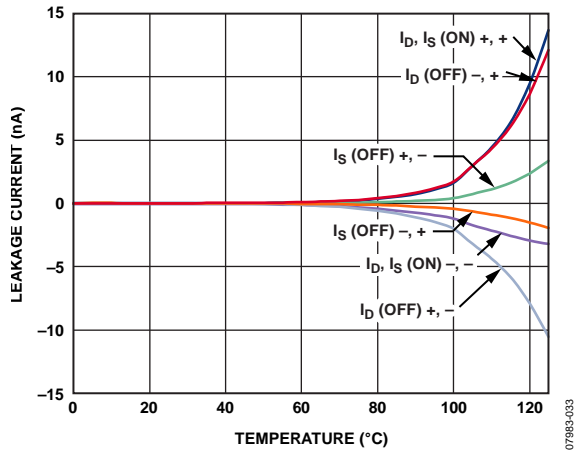


Figure 11. Leakage Currents as a Function of Temperature, ±5 V Dual Supply

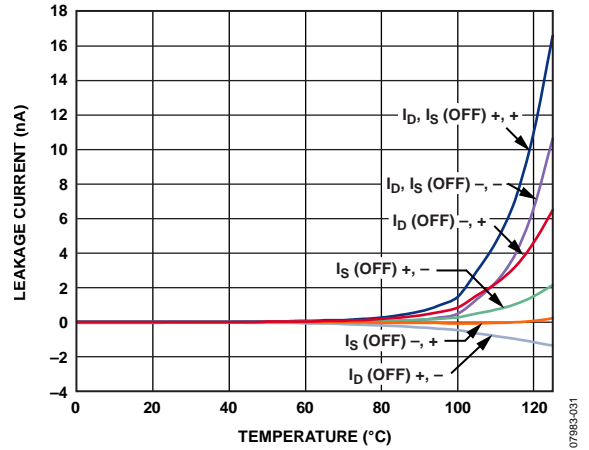


Figure 14. Leakage Currents as a Function of Temperature, 3.3 V Single Supply

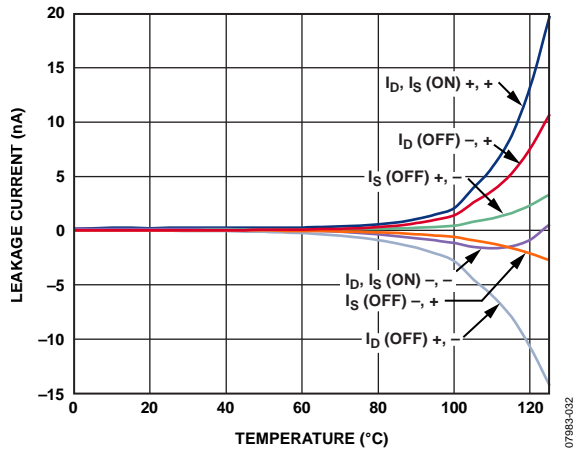


Figure 12. Leakage Currents as a Function of Temperature, 12 V Single Supply

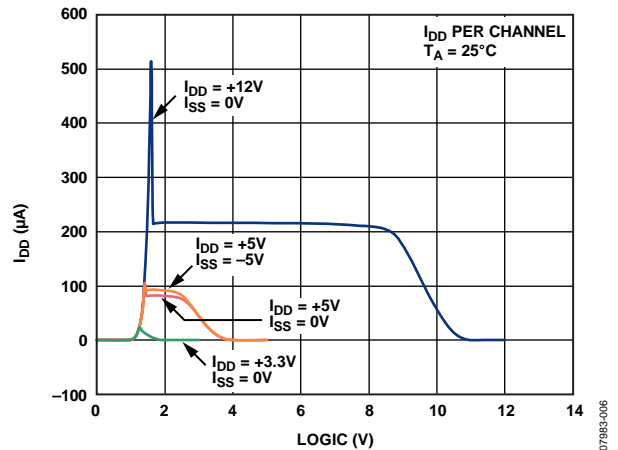


Figure 15. I_{DD} vs. Logic Level

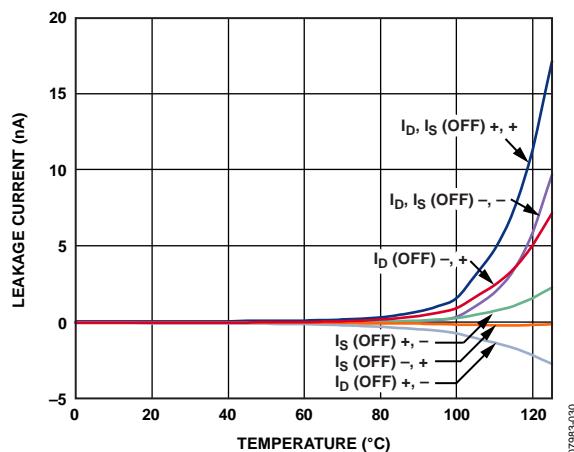


Figure 13. Leakage Currents as a Function of Temperature, 5 V Single Supply

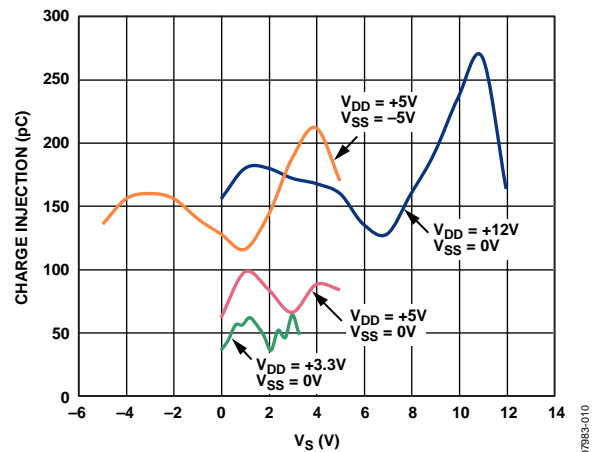


Figure 16. Charge Injection vs. Source Voltage

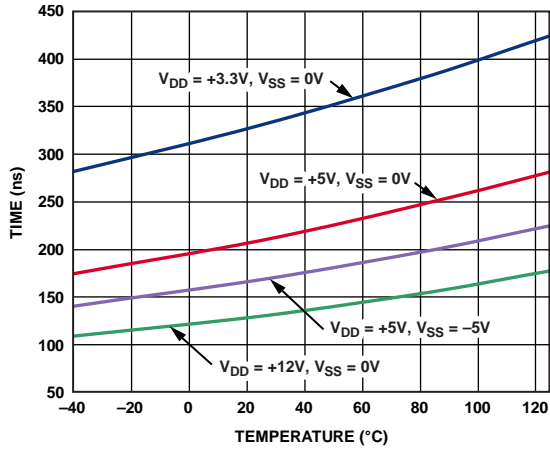


Figure 17. t_{ON}/t_{OFF} Times vs. Temperature

07983-019

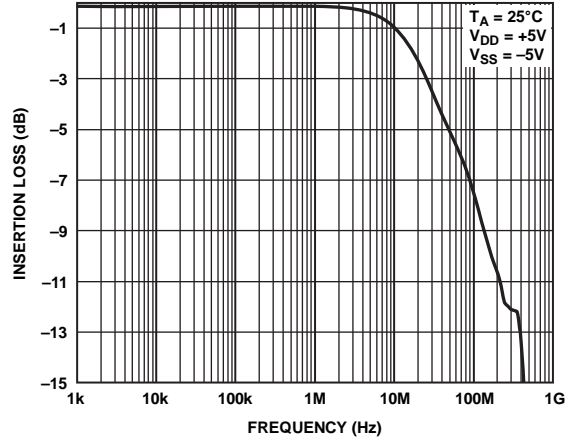


Figure 20. On Response vs. Frequency

07983-005

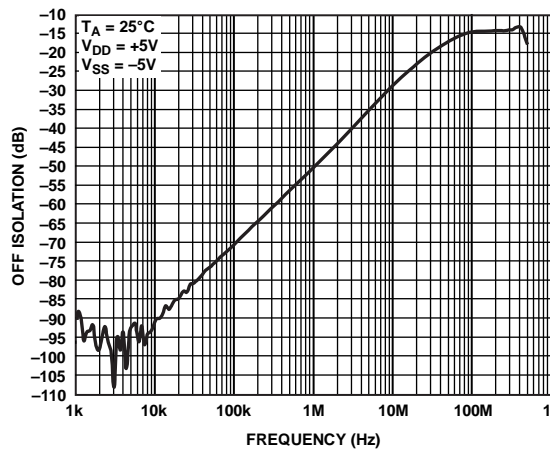


Figure 18. Off Isolation vs. Frequency

07983-008

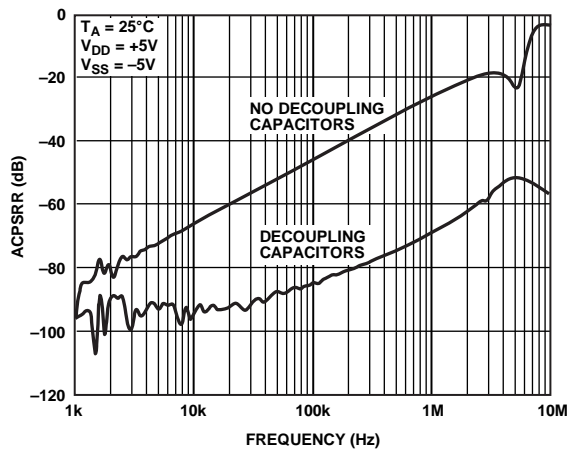


Figure 21. ACPSRR vs. Frequency

07983-009

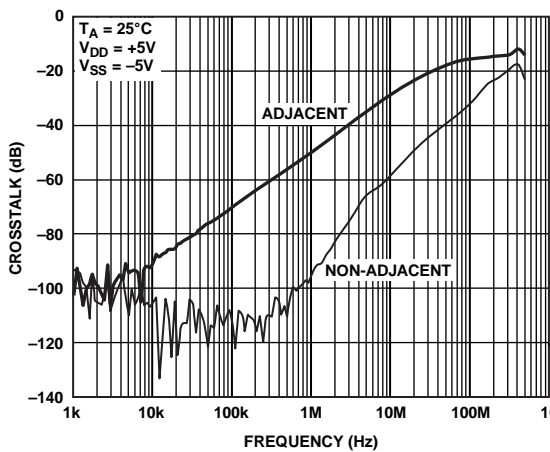


Figure 19. Crosstalk vs. Frequency

07983-018

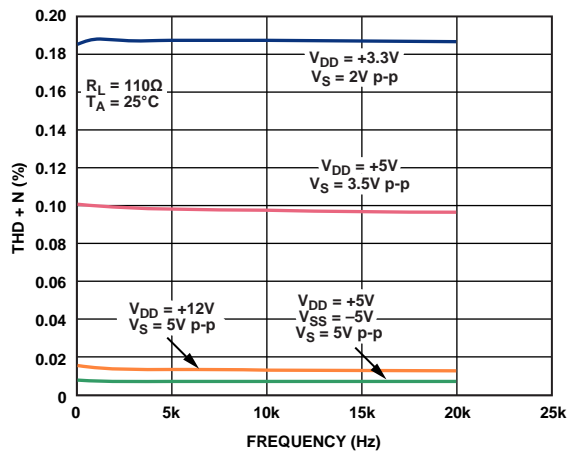


Figure 22. THD + N vs. Frequency

07983-017

TEST CIRCUITS

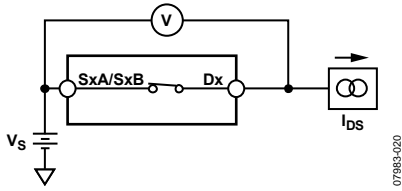


Figure 23. On Resistance

07985-020



Figure 24. Off Leakage

07983-021

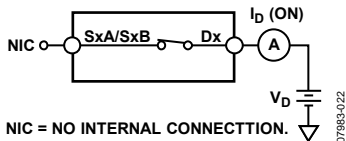
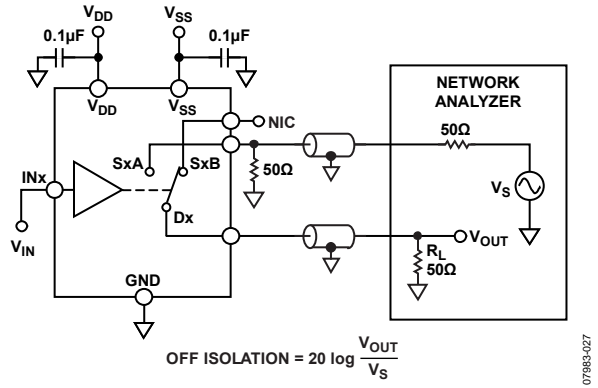


Figure 25. On Leakage

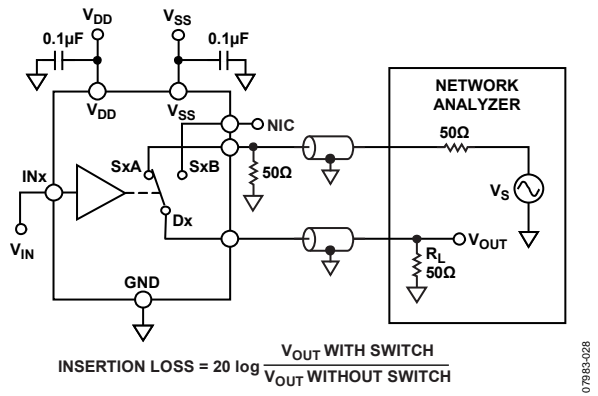
07983-022



$$\text{OFF ISOLATION} = 20 \log \frac{V_{\text{OUT}}}{V_s}$$

Figure 26. Off Isolation

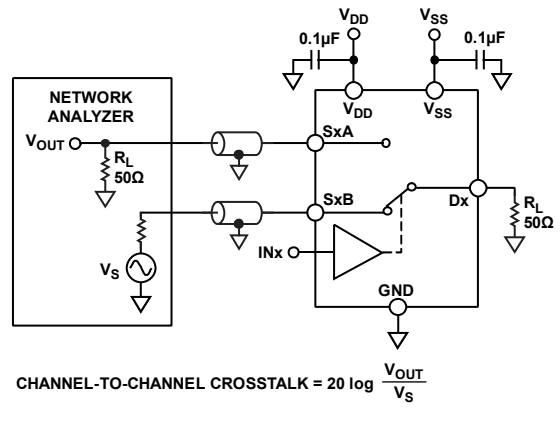
07983-027



$$\text{INSERTION LOSS} = 20 \log \frac{V_{\text{OUT WITH SWITCH}}}{V_{\text{OUT WITHOUT SWITCH}}}$$

Figure 27. Bandwidth

07983-028



$$\text{CHANNEL-TO-CHANNEL CROSSTALK} = 20 \log \frac{V_{\text{OUT}}}{V_s}$$

Figure 28. Channel-to-Channel Crosstalk

07985-029



Figure 29. THD + Noise

07983-034

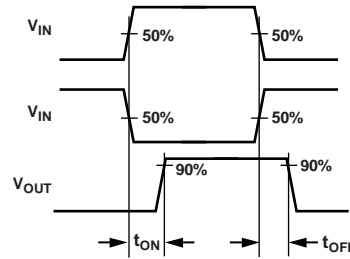


Figure 30. Switching Times

07983-023



Figure 31. Break-Before-Make Time Delay

07983-024

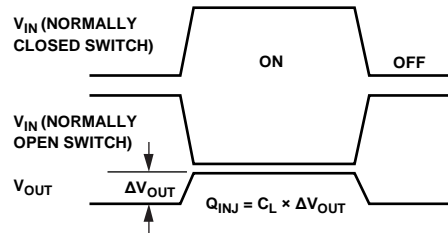


Figure 32. Charge Injection

07983-026

TERMINOLOGY

I_{DD}

The positive supply current.

I_{SS}

The negative supply current.

$V_D (V_S)$

The analog voltage on Terminal D and Terminal S.

R_{ON}

The ohmic resistance between Terminal D and Terminal S.

$R_{FLAT(ON)}$

Flatness that is defined as the difference between the maximum and minimum value of on resistance measured over the specified analog signal range.

I_S (Off)

The source leakage current with the switch off.

I_D (Off)

The drain leakage current with the switch off.

I_D, I_S (On)

The channel leakage current with the switch on.

V_{INL}

The maximum input voltage for Logic 0.

V_{INH}

The minimum input voltage for Logic 1.

$I_{INL} (I_{INH})$

The input current of the digital input.

C_S (Off)

The off switch source capacitance, which is measured with reference to ground.

C_D (Off)

The off switch drain capacitance, which is measured with reference to ground.

C_D, C_S (On)

The on switch capacitance, which is measured with reference to ground.

C_{IN}

The digital input capacitance.

$t_{TRANSITION}$

The delay time between the 50% and 90% points of the digital input and switch on condition when switching from one address state to another.

$t_{ON} (EN)$

The delay between applying the digital control input and the output switching on. See Figure 30.

$t_{OFF} (EN)$

The delay between applying the digital control input and the output switching off. See Figure 30.

Charge Injection

A measure of the glitch impulse transferred from the digital input to the analog output during switching.

Off Isolation

A measure of unwanted signal coupling through an off switch.

Crosstalk

A measure of unwanted signal that is coupled through from one channel to another as a result of parasitic capacitance.

Bandwidth

The frequency at which the output is attenuated by 3 dB.

On Response

The frequency response of the on switch.

Insertion Loss

The loss due to the on resistance of the switch.

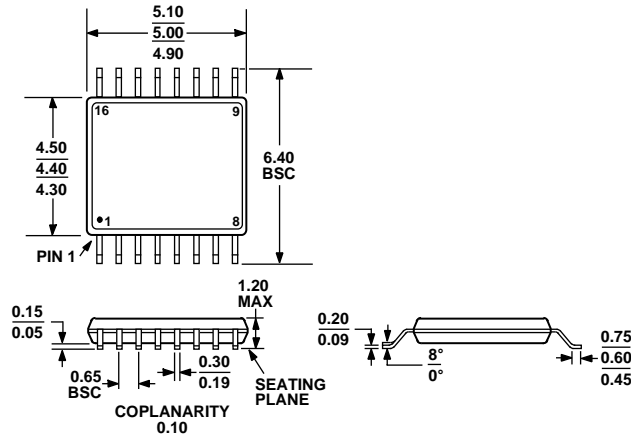
Total Harmonic Distortion + Noise (THD + N)

The ratio of the harmonic amplitude plus noise of the signal to the fundamental.

AC Power Supply Rejection Ratio (ACPSRR)

The ratio of the amplitude of signal on the output to the amplitude of the modulation. This is a measure of the ability of the device to avoid coupling noise and spurious signals that appear on the supply voltage pin to the output of the switch. The dc voltage on the device is modulated by a sine wave of 0.62 V p-p.

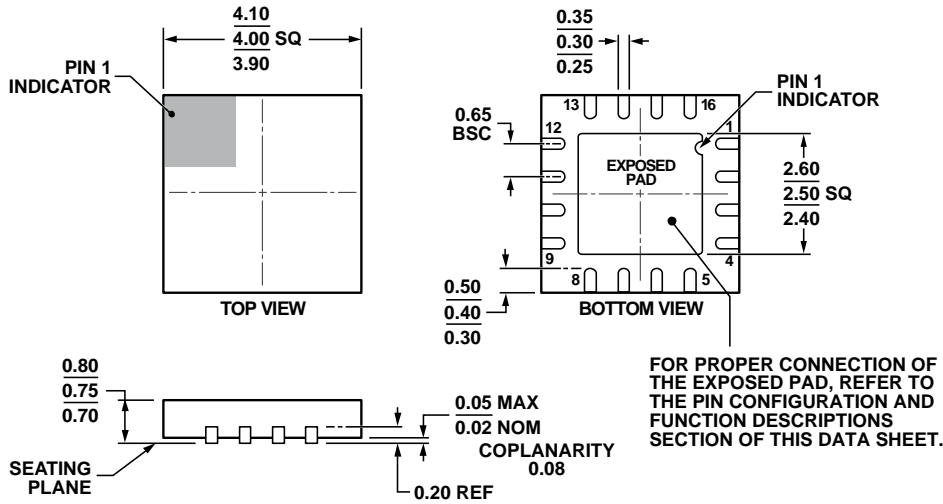
OUTLINE DIMENSIONS



COMPLIANT TO JEDEC STANDARDS MO-153-AB

Figure 33. 16-Lead Thin Shrink Small Outline Package [TSSOP] (RU-16)

Dimensions shown in millimeters



FOR PROPER CONNECTION OF THE EXPOSED PAD, REFER TO THE PIN CONFIGURATION AND FUNCTION DESCRIPTIONS SECTION OF THIS DATA SHEET.

COMPLIANT TO JEDEC STANDARDS MO-220-WGGC.

Figure 34. 16-Lead Lead Frame Chip Scale Package [LFCSOP] 4 mm x 4 mm Body and 0.75 mm Package Height (CP-16-26)

Dimensions shown in millimeters

ORDERING GUIDE

| Model ¹ | Temperature Range | Package Description | Package Option |
|--------------------|-------------------|---|----------------|
| ADG1636BRUZ | -40°C to +125°C | 16-Lead Thin Shrink Small Outline Package [TSSOP] | RU-16 |
| ADG1636BRUZ-REEL | -40°C to +125°C | 16-Lead Thin Shrink Small Outline Package [TSSOP] | RU-16 |
| ADG1636BRUZ-REEL7 | -40°C to +125°C | 16-Lead Thin Shrink Small Outline Package [TSSOP] | RU-16 |
| ADG1636BCPZ-REEL | -40°C to +125°C | 16-Lead Lead Frame Chip Scale Package [LFCSOP] | CP-16-26 |
| ADG1636BCPZ-REEL7 | -40°C to +125°C | 16-Lead Lead Frame Chip Scale Package [LFCSOP] | CP-16-26 |

¹ Z = RoHS Compliant Part.

042709-A



Компания «ЭлектроПласт» предлагает заключение долгосрочных отношений при поставках импортных электронных компонентов на взаимовыгодных условиях!

Наши преимущества:

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- Поставка более 17-ти миллионов наименований электронных компонентов;
- Поставка сложных, дефицитных, либо снятых с производства позиций;
- Оперативные сроки поставки под заказ (от 5 рабочих дней);
- Экспресс доставка в любую точку России;
- Техническая поддержка проекта, помощь в подборе аналогов, поставка прототипов;
- Система менеджмента качества сертифицирована по Международному стандарту ISO 9001;
- Лицензия ФСБ на осуществление работ с использованием сведений, составляющих государственную тайну;
- Поставка специализированных компонентов (Xilinx, Altera, Analog Devices, Intersil, Interpoint, Microsemi, Aeroflex, Peregrine, Syfer, Eurofarad, Texas Instrument, Miteq, Cobham, E2V, MA-COM, Hittite, Mini-Circuits, General Dynamics и др.);

Помимо этого, одним из направлений компании «ЭлектроПласт» является направление «Источники питания». Мы предлагаем Вам помощь Конструкторского отдела:

- Подбор оптимального решения, техническое обоснование при выборе компонента;
- Подбор аналогов;
- Консультации по применению компонента;
- Поставка образцов и прототипов;
- Техническая поддержка проекта;
- Защита от снятия компонента с производства.



Как с нами связаться

Телефон: 8 (812) 309 58 32 (многоканальный)

Факс: 8 (812) 320-02-42

Электронная почта: org@eplast1.ru

Адрес: 198099, г. Санкт-Петербург, ул. Калинина, дом 2, корпус 4, литера А.